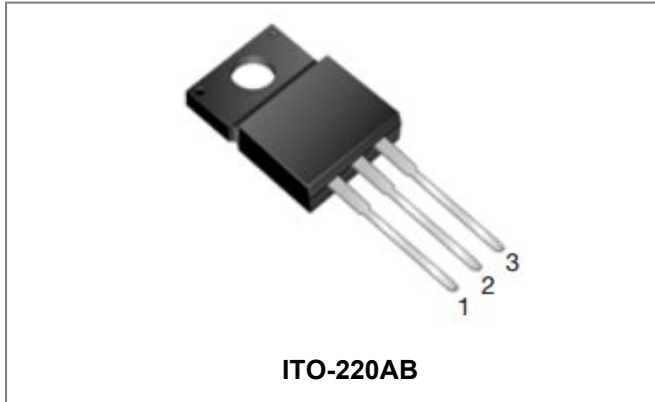


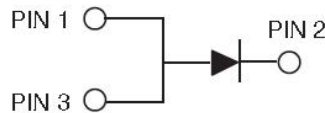
STF30100S SCHOTTKY RECTIFIER



Features

- 150 °C T_J operation
- Ultralow forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Trench MOS Schottky technology
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V _{RRM}	-	100	V
Working Peak Reverse Voltage	V _{RWM}			
DC Blocking Voltage	V _R			
Average Rectified Forward Current	I _{F(AV)}	50% duty cycle @T _c =100°C, rectangular wave form	30	A
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse, T _c =25°C	300	A

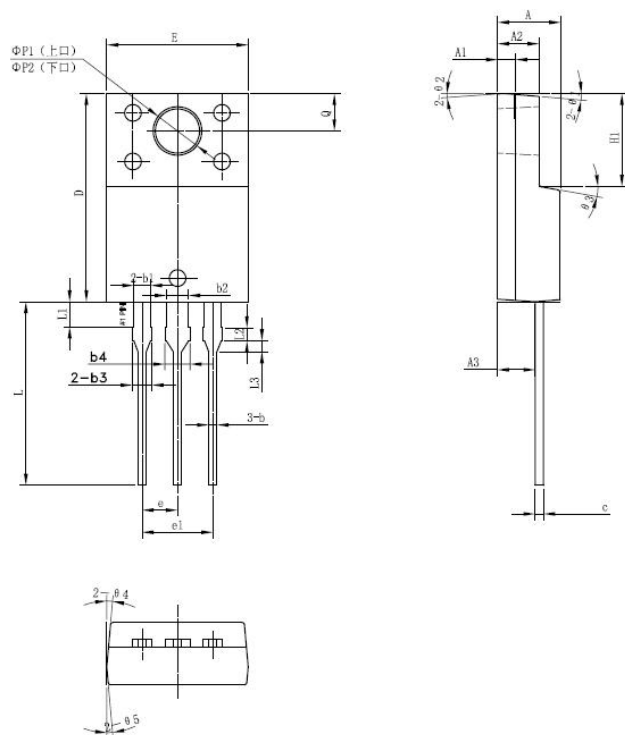
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T _J	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R _{θJC}	DC operation	5	°C/W
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop *	V _{F1}	@ 10A, Pulse, T _J = 25 °C	0.54	-	V
		@ 15A, Pulse, T _J = 25 °C	0.61	-	
@ 30A, Pulse, T _J = 25 °C		0.82	0.90		
	V _{F2}	@ 10A, Pulse, T _J = 125 °C	0.51	-	V
		@ 15A, Pulse, T _J = 125 °C	0.58	-	
		@ 30A, Pulse, T _J = 125 °C	0.74	0.78	
Reverse Current*	I _{R1}	@V _R = 70V, T _J = 25 °C	0.012	-	mA
		@V _R = 100V, T _J = 25 °C	0.030	1	
	I _{R2}	@V _R = 70V, T _J = 125 °C	10	-	mA
		@V _R = 100V, T _J = 125 °C	15	75	
Junction Capacitance	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	845	-	pF
RSM Isolation Voltage (t = 1.0 second, R. H. < =30%, T _A = 25 °C)	V _{ISO}	Clip mounting, the epoxy body away from the heatsink edge by more than 0.110" along the lead direction.	-	4500	V
		Clip mounting, the epoxy body is inside the heatsink.	-	3500	
		Screw mounting, the epoxy body is inside the heatsink.	-	1500	

* Pulse width < 300 μs, duty cycle < 2%

Mechanical Dimensions ITO-220AB


SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
b3	1.20	1.30	1.45
b4	1.60	1.70	1.85
c	0.50	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
e		2.55	
e1		5.10	
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
ΦP1(上口)	3.30	3.50	3.70
ΦP2(下口)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

Ratings and Characteristics Curves

Figure 1
Typical Forward Characteristics

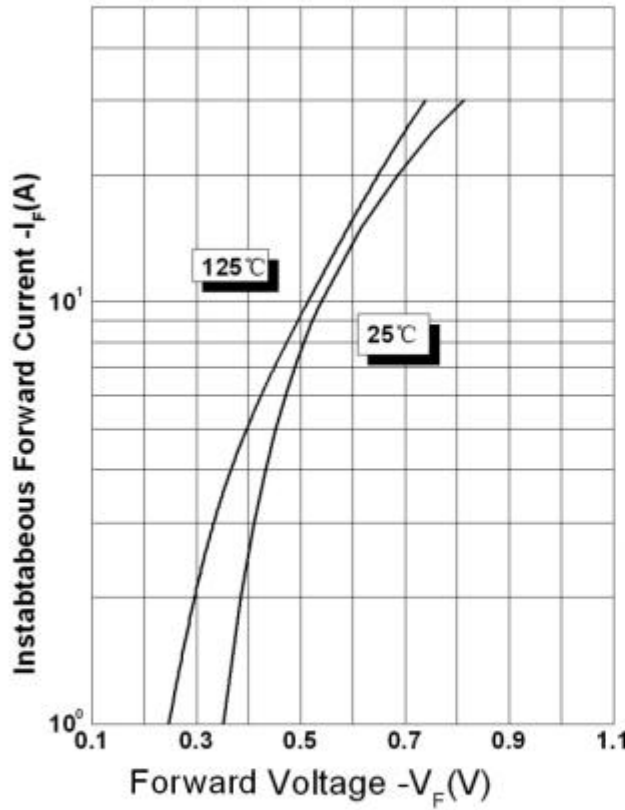


Figure 2
Typical Reverse Characteristics

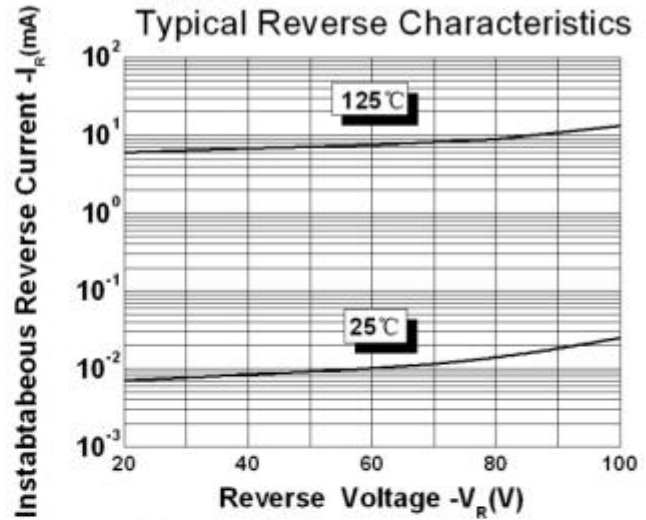
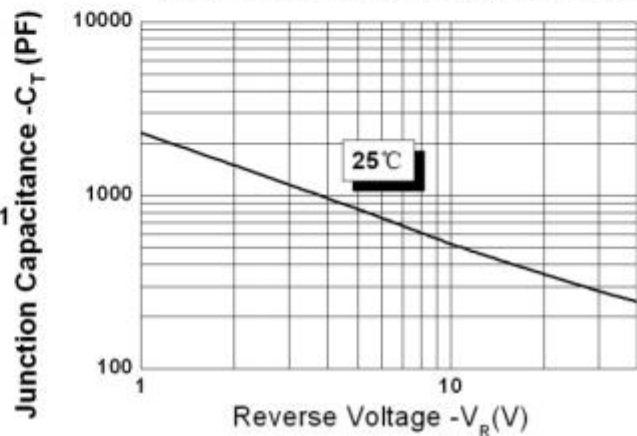
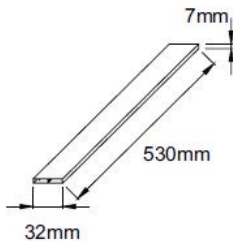


Figure 3
Typical Junction Capacitance



Tube Specification

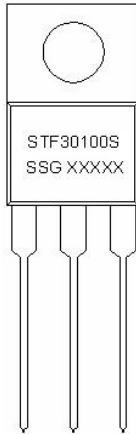


Ordering Information

Device	Package	Shipping
STF30100S	ITO-220AB (Pb-Free)	50 pcs/ tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Where XXXXX is YYWWL

ST = Device Type
 F = Package type
 30 = Forward Current (30A)
 100 = Reverse Voltage (100V)
 S = Configuration
 SSG = SSG
 YY = Year
 WW = Week
 L = Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

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